

# RJK2511DPK

Silicon N Channel MOS FET  
High Speed Power Switching

REJ03G1486-0400

Rev.4.00

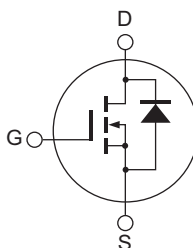
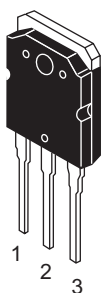
Nov 27, 2007

## Features

- Low on-resistance
- Low leakage current
- High speed switching

## Outline

RENESAS Package code: PRSS0004ZE-A  
(Package name:TO-3P)



1. Gate
2. Drain (Flange)
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	250	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	$I_D$	65	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	200	A
Body-drain diode reverse drain current	$I_{DR}$	65	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ <sup>Note1</sup>	200	A
Avalanche current	$I_{AP}$ <sup>Note3</sup>	22	A
Avalanche energy	$E_{AR}$ <sup>Note3</sup>	30.2	mJ
Channel dissipation	$P_{ch}$ <sup>Note2</sup>	200	W
Channel to case thermal impedance	$\theta_{ch-c}$	0.625	°C/W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$

2. Value at  $T_c = 25^\circ C$

3.  $ST_{ch} = 25^\circ C$ ,  $T_{ch} \leq 150^\circ C$

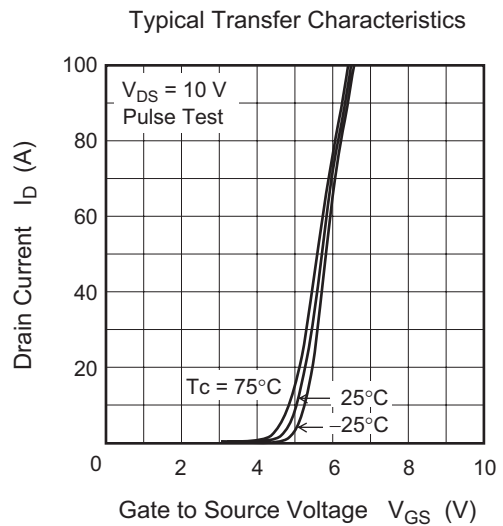
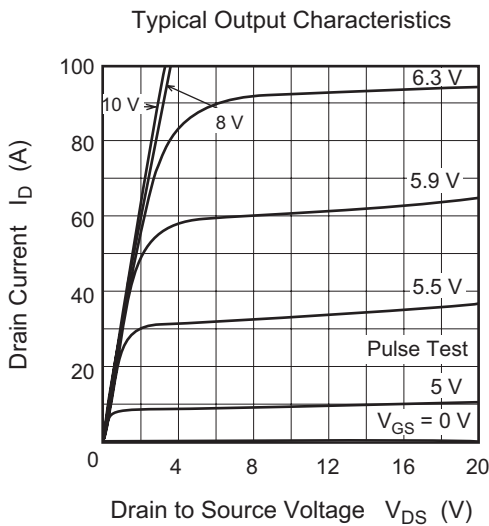
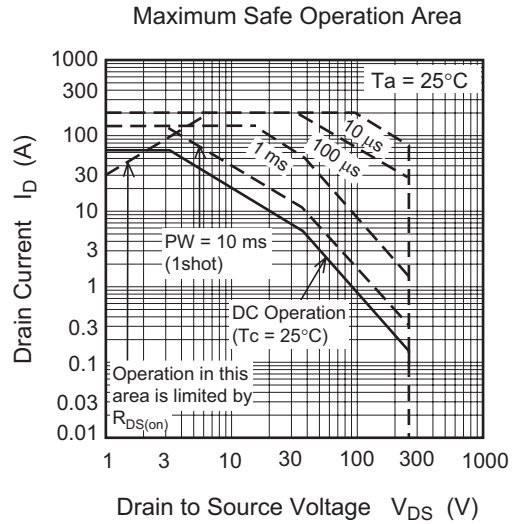
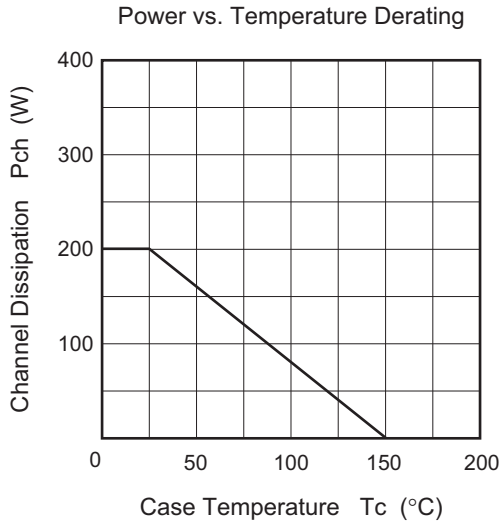
## Electrical Characteristics

(Ta = 25°C)

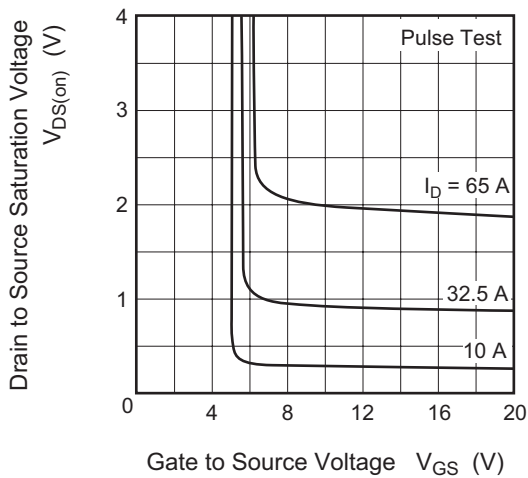
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 250 \text{ V}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	30	51	—	S	$I_D = 32.5 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Static drain to source on state resistance	$R_{DS(on)}$	—	0.028	0.034	$\Omega$	$I_D = 32.5 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	4900	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	$C_{oss}$	—	690	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	85	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	52	—	ns	$I_D = 32.5 \text{ A}$
Rise time	$t_r$	—	200	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	160	—	ns	$R_L = 3.9 \Omega$
Fall time	$t_f$	—	150	—	ns	$R_g = 10 \Omega$
Total gate charge	$Q_g$	—	120	—	nC	$V_{DD} = 200 \text{ V}$
Gate to source charge	$Q_{gs}$	—	28	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	$Q_{gd}$	—	51	—	nC	$I_D = 65 \text{ A}$
Body-drain diode forward voltage	$V_{DF}$	—	0.93	1.50	V	$I_F = 65 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>
Body-drain diode reverse recovery time	$t_{rr}$	—	200	—	ns	$I_F = 65 \text{ A}$ , $V_{GS} = 0$
Body-drain diode reverse recovery charge	$Q_{rr}$	—	1.5	—	$\mu\text{C}$	$di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

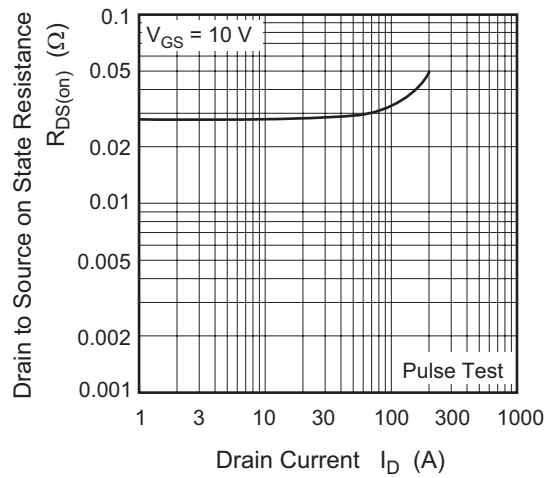
Main Characteristics

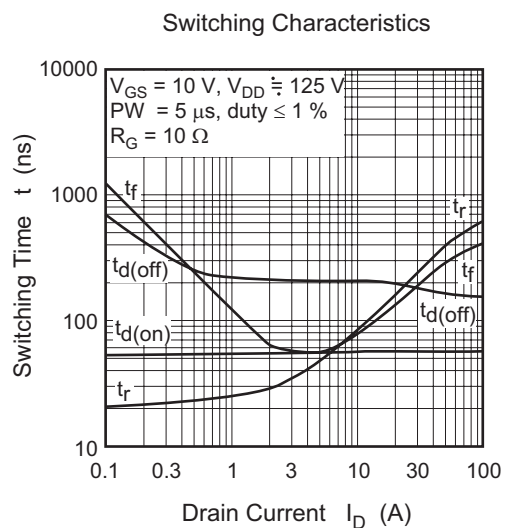
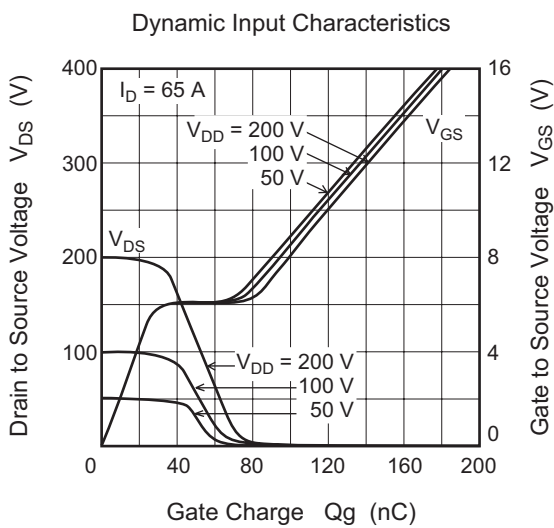
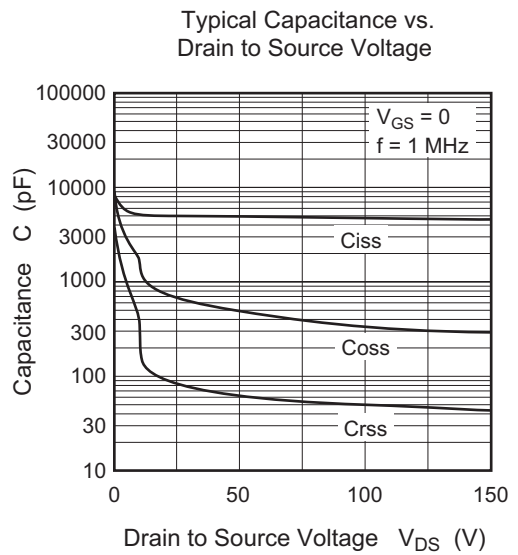
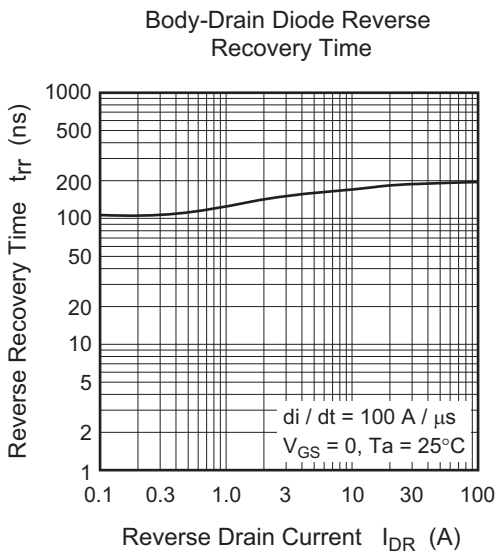
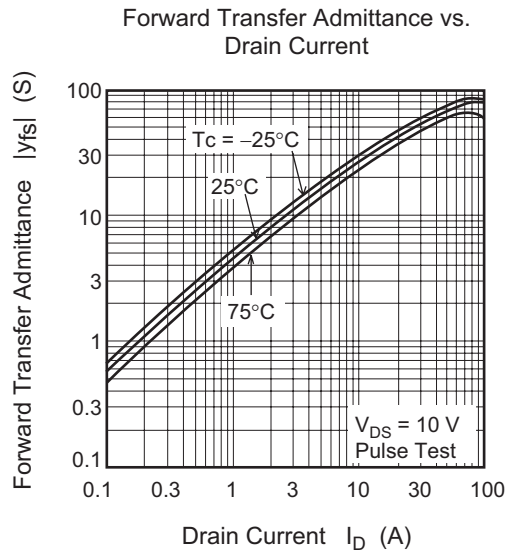
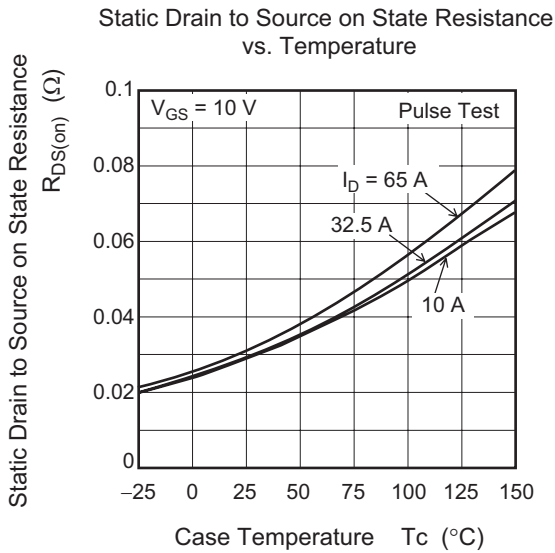


Drain to Source Saturation Voltage vs. Gate to Source Voltage

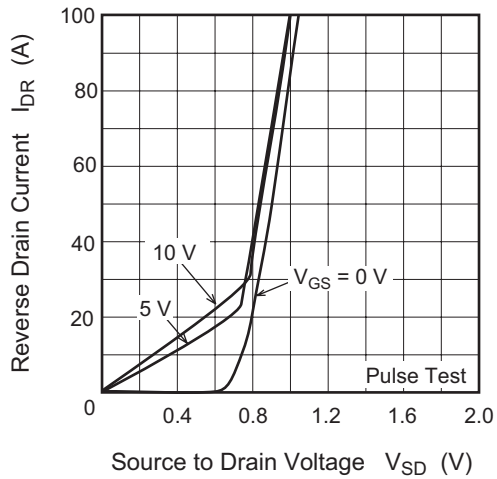


Static Drain to Source on State Resistance vs. Drain Current

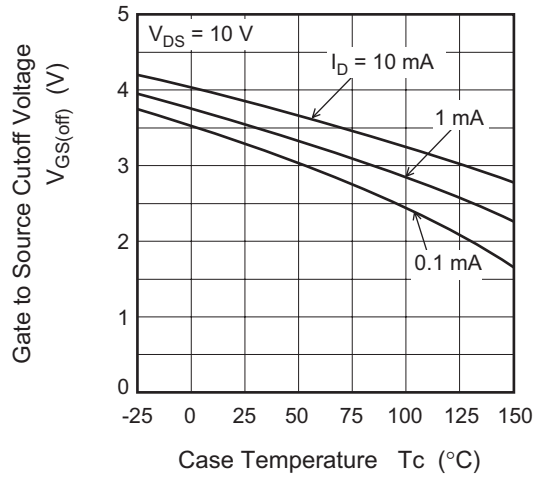




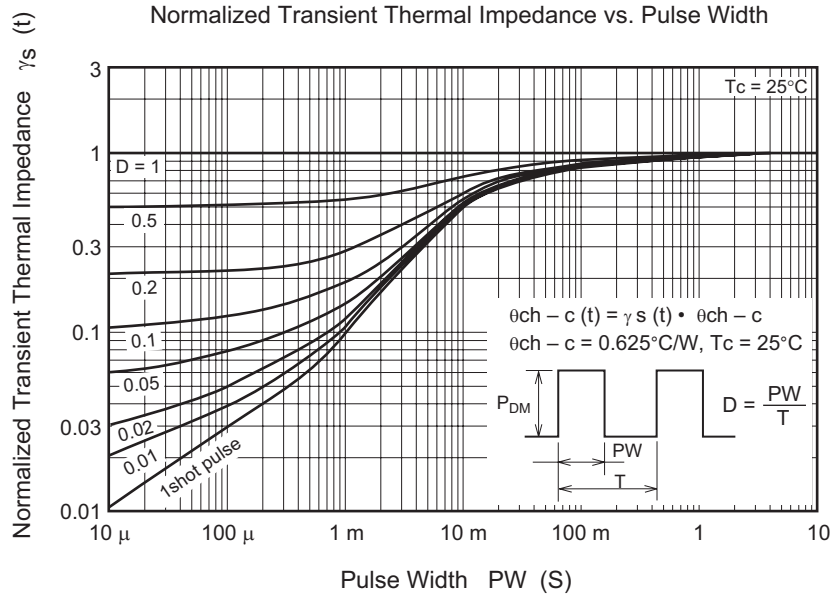
Reverse Drain Current vs. Source to Drain Voltage



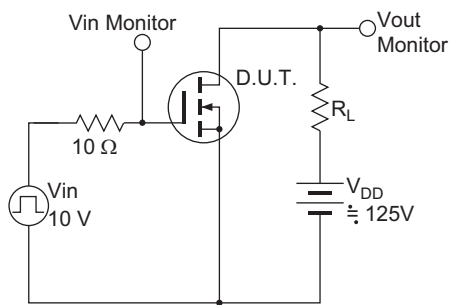
Gate to Source Cutoff Voltage vs. Case Temperature



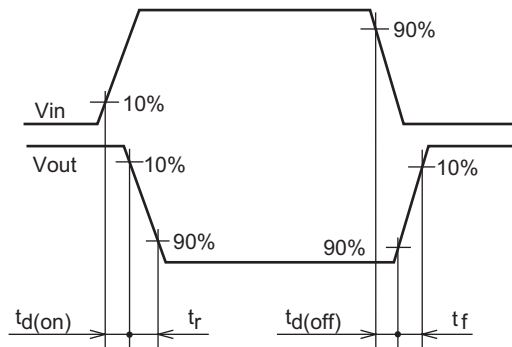
Normalized Transient Thermal Impedance vs. Pulse Width



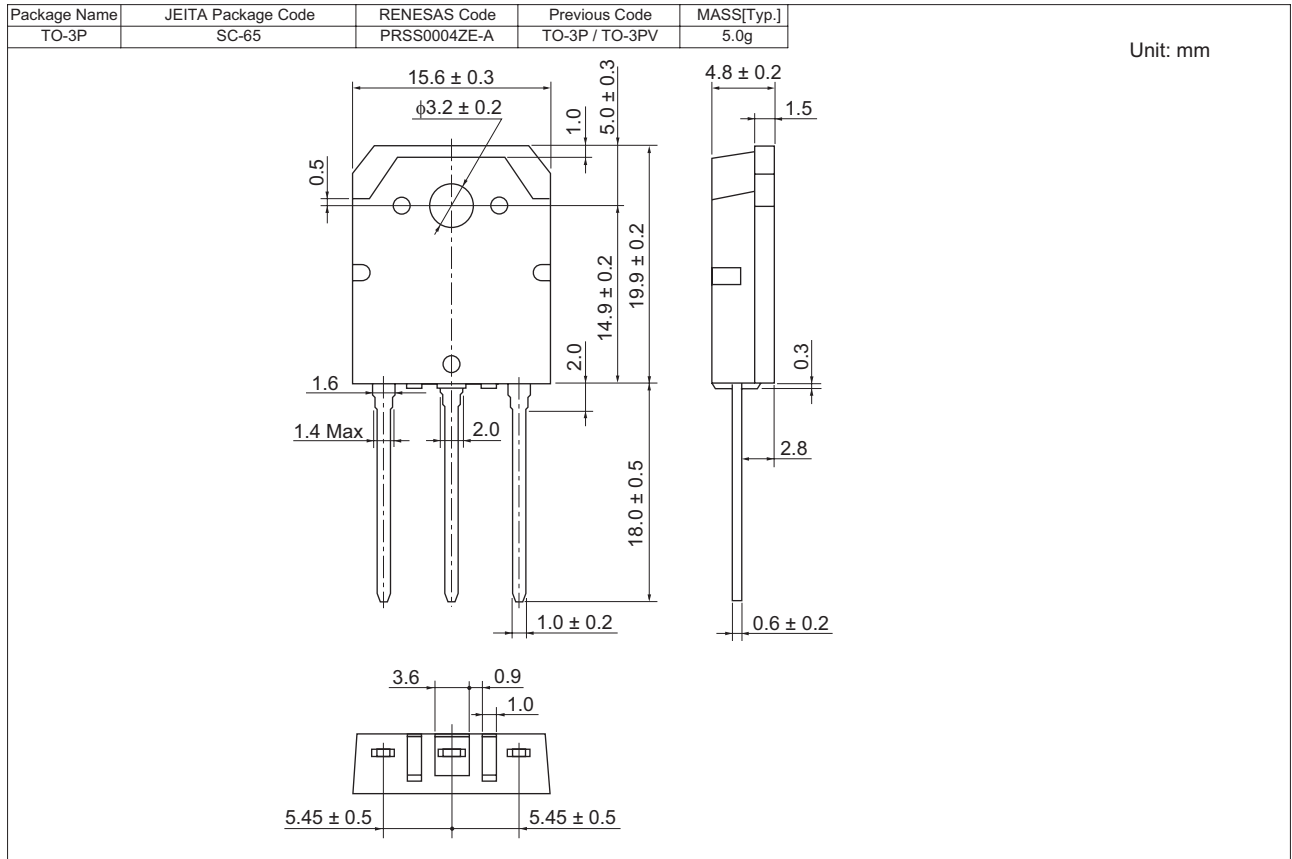
Switching Time Test Circuit



Waveform



### Package Dimensions



### Ordering Information

Part No.	Quantity	Shipping Container
RJK2511DPK-00-T0	360 pcs	Box (Tube)

Notes:

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Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

**Renesas Technology Europe Limited**  
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**Renesas Technology Taiwan Co., Ltd.**  
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Tel: <65> 6213-0200, Fax: <65> 6278-8001

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Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea  
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

**Renesas Technology Malaysia Sdn. Bhd**  
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: <603> 7955-9390, Fax: <603> 7955-9510